MSKSEMI 美森科













ESD

TV

TSS

MOV

GDT

 PLED

RCLAMP0521T

Product specification





Features

- 100Watts peak pulse power (tp = 8/20μs)
- Bidirectional configurations
- Solid-state silicon-avalanche technology
- Low clamping voltage
- Low leakage current
- Low capacitance (Cj=0.25pF typ. IO to IO)
- Protection one data/power line to:
 IEC 61000-4-2 ±20kV contact ±20kV air
 IEC 61000-4-4 (EFT) 40A (5/50ns)

IEC 61000-4-5 (Lightning) 4A (8/20μs)

Applications

- Cell Phone Handsets and Accessories
- Microprocessor based equipment
- Personal Digital Assistants (PDA's)
- Notebooks, Desktops, and Servers
- Portable Instrumentation

Mechanical Data

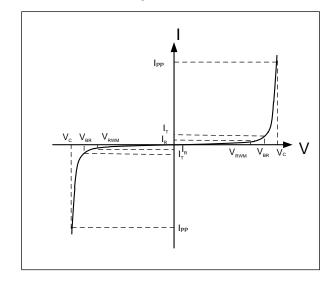
- DFN1006-2L
- Molding compound flammability rating: UL 94V-0
- Packaging: Tape and Reel
- RoHS/WEEE Compliant

Reference News

PACKAGE OUTLINE	Circuit Diagram	Marking
DFN1006-2L		N

Electrical Parameters (TA = 25°C unless otherwise noted)

Symbol	Parameter
IPP	Maximum Reverse Peak Pulse Current
Vc	Clamping Voltage @ IPP
V _{RWM}	Working Peak Reverse Voltage
I_R	Maximum Reverse Leakage Current @ VRWM
V _{BR}	Breakdown Voltage @ IT
Iτ	Test Current





Absolute Maximum Rating

Rating	Symbol	Value	Units
Peak Pulse Power (t _p =8/20µs)	P _{PP}	100	Watts
Peak Pulse Current (t _p =8/20µs) (note1)	I _{pp}	4.0	А
ESD per IEC 61000-4-2 (Air) ESD per IEC 61000-4-2 (Contact)	V _{ESD}	20 20	kV
Lead Soldering Temperature	TL	260(10seconds)	${\mathbb C}$
Junction Temperature	TJ	-55 to + 125	$^{\circ}$
Storage Temperature	T _{stg}	-55 to + 125	$^{\circ}$

Electrical Characteristics

Parameter	Symbol	Conditions	Min	Typical	Max	Units
Reverse Stand-Off Voltage	V_{RWM}				5.0	V
Reverse Breakdown Voltage	V_{BR}	I _T =1mA	6.0			V
Reverse Leakage Current	I _R	V _{RWM} =5V,T=25℃			100	nA
Peak Pulse Current	I _{PP}	tp =8/20µs			4.0	Α
Clamping Voltage	Vc	I _{PP} =4A,t _p =8/20μs			25	V
Junction Capacitance	Cj	IO to IO $V_R = 0V, f = 1MHz$		0.25	0.5	pF



TypicalCharacteristics

Figure 1: Peak Pulse Power vs. Pulse Time

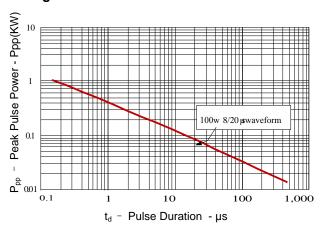


Figure 3: Pulse Waveform

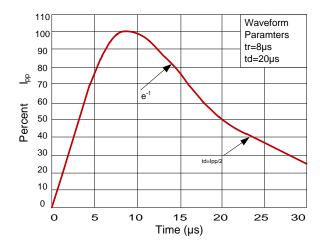


Figure5: Positive Clamping voltage (TLP)

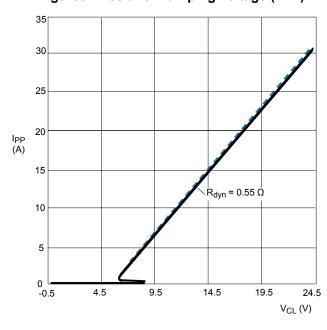


Figure 2: Power Derating Curve

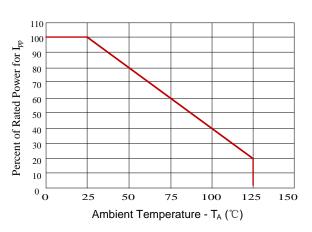


Figure 4: Clamping Voltage vslpp

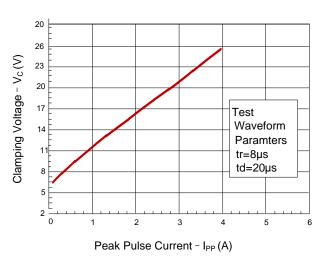
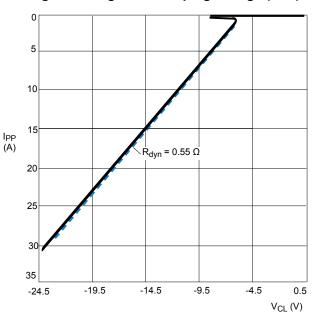
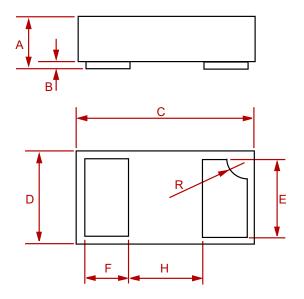


Figure 5: Negative Clamping voltage (TLP)



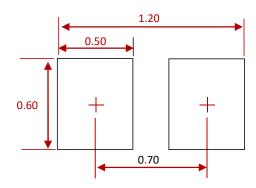


PACKAGE MECHANICAL DATA



Dim	Inches		Millimeters		
Dim	MIN	MAX	MIN	MAX	
Α	0.0125	0.02	0.32	0.52	
В	0.000	0.002	0.00	0.05	
С	0.037	0.043	0.95	1.080	
D	0.022	0.027	0.55	0.680	
E	0.016	0.024	0.40	0.60	
F	0.008	0.012	0.20	0.30	
Н	0.015Typ.		0.40Тур.		
R	0.001	0.005	0.05	0.15	

Suggested Pad Layout



NOTES:

- 1. CONTROLLING DIMENSIONS ARE IN MILLIMETERS (ANGLES IN DEGREES).
- 2. THIS LAND PATTERN IS FOR REFERENCE PURPOSES ONLY. CONSULT YOUR MANUFACTURING GROUP TO ENSURE YOUR COMPANY'S MANUFACTURING GUIDELINES ARE MET.

REEL SPECIFICATION

P/N	PKG	QTY
RCLAMP0521T	DFN1006-2L	10000



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